

Dual digital transistors

US6H23

●Features

In addition to the features of regular digital transistors.

1) Low saturation voltage, typically

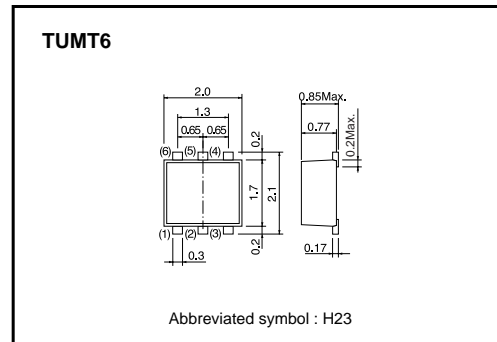
$V_{CE(sat)}=40\text{mV}$ at $I_C / I_B=50\text{mA} / 2.5\text{mA}$, makes these transistors ideal for muting circuits.

2) These transistors can be used at high current levels,
 $I_C=600\text{mA}$.

●Structure

NPN silicon epitaxial planar transistor

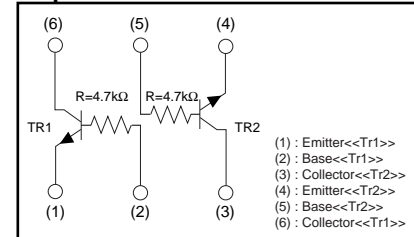
●Dimensions (Unit : mm)



●Packaging specifications and h_{FE}

Type	Package	TUMT6
	Packaging type	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
US6H23		○

●Equivalent circuit



●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	12	V
Collector current	I_C	600	mA
	I_{CP}	1	A *1
Power dissipation	P_D	0.4(TOTAL)	W *2
		1.0(TOTAL)	W *3
		0.7(ELEMENT)	W *3
Junction temperature	T_j	150	$^\circ\text{C}$
Range of storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

*1 $P_w=10\text{ms}$ 1 Pulse

*2 Each terminal mounted on a recommended land

*3 Mounted on a ceramic board

Transistor

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	20	–	–	V	$I_C=1\text{mA}$
Collector-base breakdown voltage	BV_{CBO}	20	–	–	V	$I_C=50\mu\text{A}$
Emitter-base breakdown voltage	BV_{EBO}	12	–	–	V	$I_E=50\mu\text{A}$
Collector cutoff current	I_{CBO}	–	–	500	nA	$V_{CB}=20\text{V}$
Emitter cutoff current	I_{EBO}	–	–	500	nA	$V_{EB}=12\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	40	150	mV	$I_C / I_B=50\text{mA} / 2.5\text{mA}$
DC current gain	h_{FE}	820	–	2700	–	$V_{CE}=5\text{V}, I_C=50\text{mA}$
Transition frequency	f_T *	–	150	–	MHz	$V_{CE}=10\text{V}, I_E=50\text{mA}, f=100\text{MHz}$
Collector output capacitance	C_{ob} *	–	6	–	pF	$V_{CB}=10\text{V}, I_E=0\text{mA}, f=1\text{MHz}$
Input resistance	R	3.29	4.7	6.11	k Ω	–
Output ON resistance	R_{on}	–	0.55	–	Ω	$V_I=5\text{V}, R_L=1\text{k}\Omega, f=1\text{kHz}$

*Characteristics of built-in transistor.

● R_{on} measurement circuit

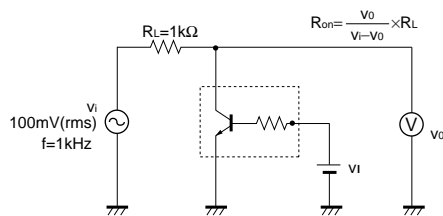


Fig.1 Output "ON" resistance (R_{on}) measurement circuit

Transistor

●Electrical characteristic curves

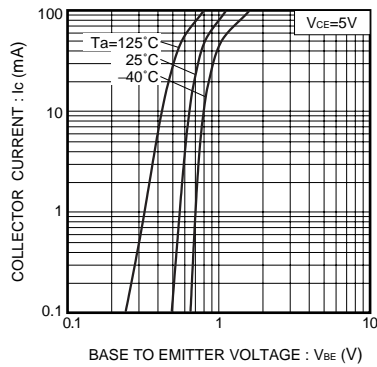


Fig.1 Grounded emitter propagation characteristics

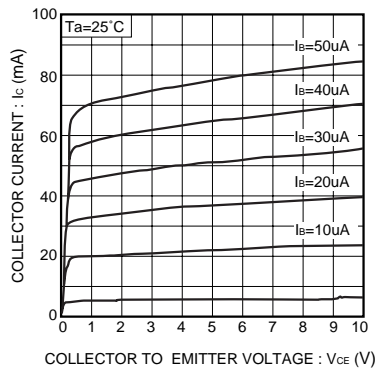


Fig.2 Typical output characteristics

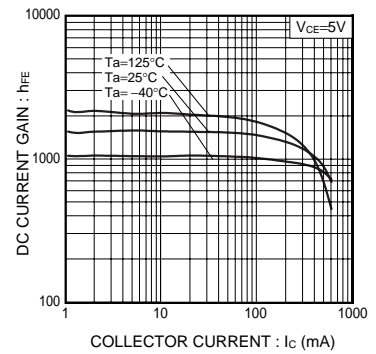


Fig.3 DC current gain vs. collector current

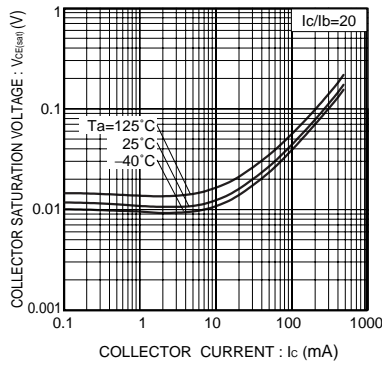


Fig.4 Collector-emitter saturation voltage vs. collector current

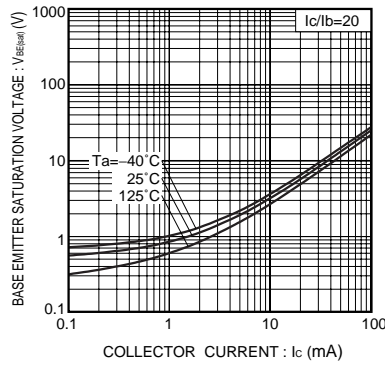


Fig.5 Base-emitter saturation voltage vs. collector current

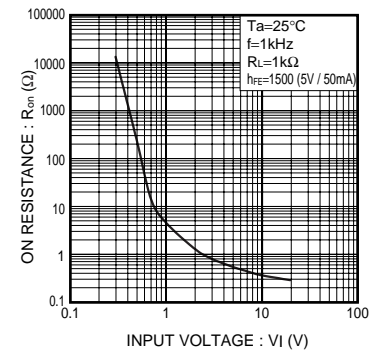


Fig.6 "ON" resistance vs. input voltage

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